

Measurements of NitroStrip detectors irradiated with protons and neutrons

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Nitrogen enriched material showed an improvement of some defects after irradiation. NitroStrip is a RD50 project that aims to compare nitrogen enriched silicon wafers with FZ, DOFZ and MCz material. This presentation will show laser measurements and electrical characterization of NitroStrip samples irradiated at different fluences with protons and neutrons.

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